

REMARKS

Examiner Le is thanked for the thorough search and examination of the subject patent application and for withdrawing the finality of the rejection of the last office action. Claims 81-82 and 87-93 have been canceled. The title has been correctly noted in this office action. The Examiner is thanked for noticing this error.

Reconsideration of the rejection of claims 83, and 94-95 under 35 U.S.C. 112, second paragraph, is requested in accordance with the following remarks. The paragraph bridging pages 20 and 21 of the Specification states:

Removal of electrons from the nitride region during erase can be done by hot hole injection from the nitride region to the diffusion, or by F-N tunneling from the nitride region to the control gate. In the hot hole injection method, the substrate is grounded, diffusions are set to 5V and negative 5V is applied to the control gate. For F-N tunneling, a negative 3.5V is applied to both the substrate and diffusions and positive 5V is applied to the control gates. A block of nitride regions must be erased at once. A single nitride region cannot be erased.

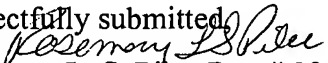
This paragraph provides the subject matter for:

“providing a first voltage to said bit line diffusions; and

providing a second voltage opposite to said first voltage to said control gate over said bit line diffusions.” (Claim 83)

The claims do not claim that the voltages have the same magnitude, but that they have opposite positive/negative aspects.

It is requested that should Examiner Le not find that the Claims are Allowable that he call the undersigned at 765 4530866 to overcome any problems preventing allowance.

Respectfully submitted,  
  
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